



#### 100V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>C</sub> = +25°C
	22mΩ @ V <sub>GS</sub> = 10V	51.7A
100V	30mΩ @ V <sub>GS</sub> = 6V	44.3A
	43.7mΩ @ V <sub>GS</sub> = 4.5V	36.7A

### Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

## **Applications**

- Power Management Functions
- DC-DC Converters
- Backlighting

## **Features**

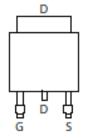
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R<sub>DS(ON)</sub> Minimizes Power Losses
- Low Q<sub>G</sub> Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMTH10H025LK3Q</u>)

#### **Mechanical Data**

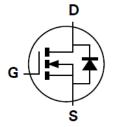
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 🔞
- Weight: 0.33 grams (Approximate)



Top View



Pin Out Top View



**Equivalent Circuit** 

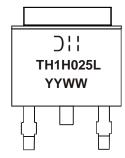
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH10H025LK3-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



DII = Manufacturer's Marking
TH1H025L = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 18 = 2018)
WW = Week Code (01 to 53)

July 2018

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# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	100	V	
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current, $V_{GS} = 10V$ (Note 6) $T_C = +25^{\circ}C$ $T_C = +100^{\circ}C$		I <sub>D</sub>	51.7 36.6	А
Pulsed Drain Current (10µs Pulse, T <sub>C</sub> = +25°C, Package Limited )	I <sub>DM</sub>	200	А	
Maximum Continuous Body Diode Forward Current (Note 6)		I <sub>S</sub>	77	А
Pulsed Body Diode Forward Current (10µs Pulse, T <sub>C</sub> = +25°C, Package Limited)		I <sub>SM</sub>	200	А
Avalanche Current, L = 0.1mH		I <sub>AS</sub>	15.8	А
Avalanche Energy, L = 0.1mH		E <sub>AS</sub>	12.5	mJ

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P <sub>D</sub>	3.1	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	48	°C/W
Total Power Dissipation (Note 6)		P <sub>D</sub>	100	W
Thermal Resistance, Junction to Case (Note 6)		R <sub>0JC</sub>	1.5	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	_	_	V	$V_{GS} = 0V$ , $I_D = 1mA$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 80V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
		_	17.1	22		$V_{GS} = 10V, I_D = 20A$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	21.4	30	mΩ	$V_{GS} = 6V, I_D = 20A$
	' ' '	_	28.3	43.7		$V_{GS} = 4.5V, I_D = 20A$
Diode Forward Voltage	V <sub>SD</sub>	_	_	1.3	V	$V_{GS} = 0V, I_S = 20A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C <sub>iss</sub>	_	1477	_		50///
Output Capacitance	Coss	_	263	_	pF	$V_{DS} = 50V$ , $V_{GS} = 0V$ f = 1MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	20	_		
Gate Resistance	R <sub>G</sub>	_	1.3	_	$\Omega$ $V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MH$	
Total Gate Charge	Q <sub>G</sub>	_	21	_		
Gate-Source Charge	Q <sub>GS</sub>	_	5.7	_	nC	$V_{DD} = 50V, I_D = 20A,$
Gate-Drain Charge	Q <sub>GD</sub>	_	3.8	_		$V_{GS} = 10V$
Turn-On Delay Time	t <sub>D(ON)</sub>	_	6.3	_		
Turn-On Rise Time	t <sub>R</sub>	_	9.4	_	7.5	$V_{DD} = 50V, V_{GS} = 10V,$
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	16.7	_	ns	$I_D = 20A$ , $R_G = 6\Omega$
Turn-Off Fall Time	t <sub>F</sub>	_	8.2	_		
Reverse Recovery Time	t <sub>RR</sub>	_	38.7	_	ns	
Reverse Recovery Charge	Q <sub>RR</sub>	_	53.7	_	nC	I <sub>F</sub> = 20A, di/dt = 100A/μs

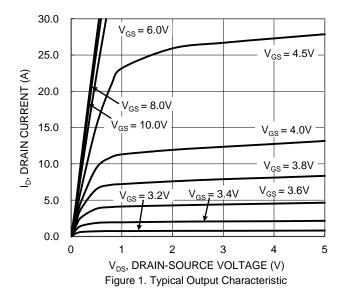
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

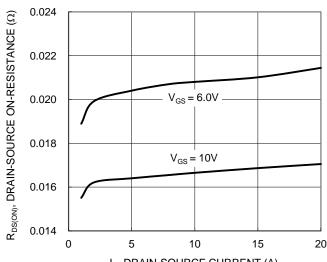
6. Thermal resistance from junction to soldering point (on the exposed drain pad).

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.







I<sub>D</sub>, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

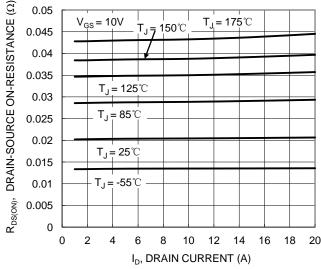
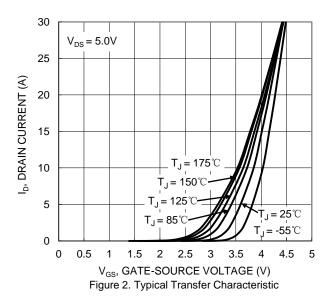


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



 $R_{DS(ON)}$ , DRAIN-SOURCE ON-RESISTANCE  $(\Omega)$ 0.2 0.15 0.1 0.05  $I_{\rm D} = 20A$ 0 2 4 6 8 10 12 14 16 18 20 V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Figure 4. Typical Transfer Characteristic

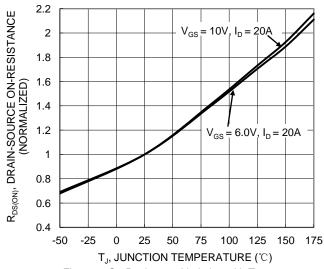


Figure 6. On-Resistance Variation with Temperature



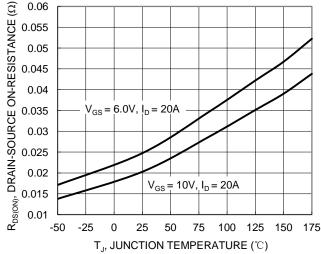


Figure 7. On-Resistance Variation with Temperature

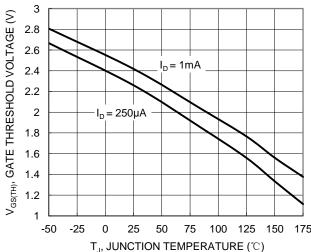


Figure 8. Gate Threshold Variation vs. Junction Temperature

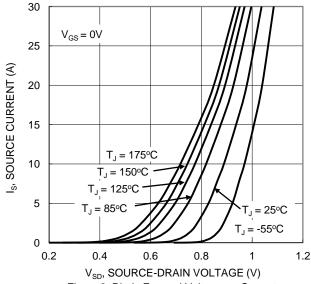
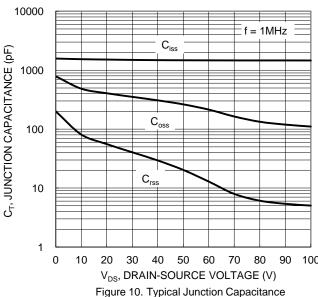


Figure 9. Diode Forward Voltage vs. Current



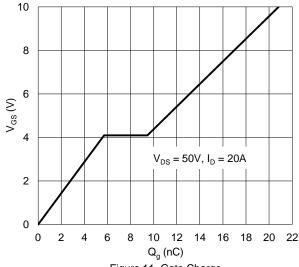
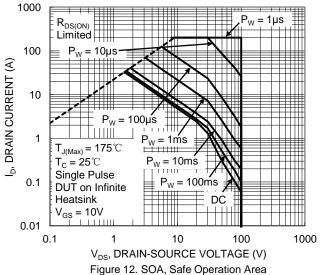


Figure 11. Gate Charge





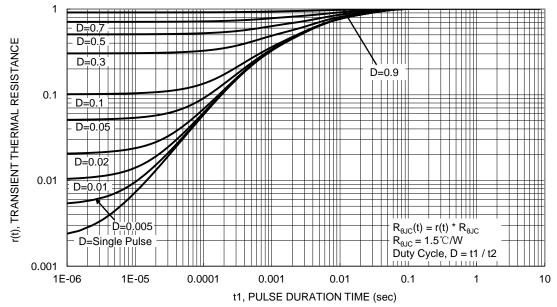


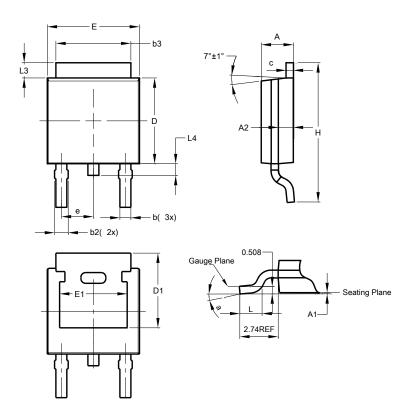
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

## TO252 (DPAK)

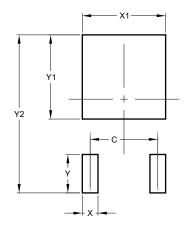


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
<b>A1</b>	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
q	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
O	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
П	6.45	6.70	6.58		
E1	4.32	-	-		
H	9.40	10.41	9.91		
Г	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **TO252 (DPAK)**



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Υ	2.600		
Y1	5.700		
Y2	10.700		



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